

IN THE CLAIMS:

Please cancel claims 17 and 18 without prejudice to or disclaimer of the subject matter recited therein.

Please amend claims 1-3, 6-9, 11-12 and 14 as follows:

LISTING OF CURRENT CLAIMS

Claim 1. (Currently Amended) A process for making an integrated circuit package comprising:

providing a substrate having a chip-attaching surface;

5 applying an A-stage liquid paste on the chip-attaching surface of the substrate, the A-stage liquid paste including a thermosetting material and a solvent;
heating the substrate to remove the solvent of the A-stage liquid paste in a manner that the A-stage liquid paste is transformed into a dry B-stage film layer;

10 attaching a chip to the chip-attaching surface of the substrate by using the B-stage film layer as an adhesive, the B-stage film layer being ~~active-without fully cured;~~ maintained in a partially cured condition;

electrically connecting the chip with the substrate having the B-stage film layer; and

15 forming a molding compound on the chip-attaching surface of the substrate, ~~the a~~ a packing pressure for the molding compound being larger than ~~the a~~ a chip-attaching pressure in a manner that the B-stage film layer re-bonds to the chip to improve effective chip-bonding area.

Claim 2. (Currently Amended) The process in accordance with claim 1, wherein the packing pressure is ~~4000psi-1500psi~~ 1000psi (6.9MPa) to 1500 psi (10.3 MPa) during the forming step of the molding compound.

Claim 3. (Currently Amended) The process in accordance with claim 1, wherein ~~an a~~ a temperature is provided from 150°C to 200°C during the forming step of the molding compound to transform the B-stage film layer into a C-stage film layer.

Claim 4. (Original) The process in accordance with claim 3, wherein the temperature in the forming step of the molding compound is larger than the temperature in the heating step of the substrate.

Claim 5. (Original) The process in accordance with claim 1, wherein the B-stage film has a glass transition temperature (T_g) higher than -10°C.

Claim 6. (Currently Amended) The process in accordance with claim 5, wherein the ~~chip-attaching~~ chip-attaching temperature is higher than the glass transition temperature (T_g) of the B-stage film layer.

Claim 7. (Currently Amended) The process in accordance with claim 1, wherein the A-stage liquid paste is ~~formed~~ applied by one of a group consisting of printing, screen printing, ~~stencil~~ stencil printing, spraying, spin coating ~~or~~ and dipping.

Claim 8. (Currently Amended) The process in accordance with claim 1, wherein the B-stage film layer is bonded ~~with the~~ to a back surface of the chip.

Claim 9. (Currently Amended) The process in accordance with claim 1, wherein the B-stage film layer is bonded ~~with the~~ to an active surface of the chip.

Claim 10. (Original) The process in accordance with claim 1, wherein the B-stage film layer and the molding compound are cured simultaneously during the forming step of the molding compound.

Claim 11. (Currently Amended) A process for making an integrated circuit package comprising:

providing a substrate having a chip-attaching surface;

applying an A-stage liquid paste on the chip-attaching surface of the

5 substrate;

heating a substrate to transform the A-stage liquid paste into a B-stage film layer;

the B-stage film layer having a glass transition temperature (T_g);

10 attaching a chip to the chip-attaching surface of the substrate, the substrate is being heated ~~being~~ higher than the glass transition temperature (T_g) of the B-stage film layer to make the B-stage film layer adhere to the substrate ~~and with~~ the chip, and the B-stage film layer being ~~active without fully cured~~; maintained in a partially cured condition;

15 electrically connecting the attached chip ~~with~~ to the substrate having the B-stage film layer; and

forming a molding compound over the electrically-connected chip on the chip-attaching surface of the substrate, ~~the~~ a packing pressure for the molding compound being larger than ~~the~~ a chip-attaching pressure in a manner that the B-stage film layer re-bonds to the chip to improve effective chip-bonding area.

Claim 12. (Currently Amended) The process in accordance with claim 11, wherein the packing pressure is ~~1000psi-1500psi~~ 1000psi (6.9MPa) to 1500 psi (10.3 MPa) during the forming step of the molding compound.

Claim 13. (Original) The process in accordance with claim 11, wherein the B-stage film layer and the molding compound are cured simultaneously during the forming step of the molding compound.

Claim 14. (Currently Amended) The process in accordance with claim 13, wherein ~~an~~ a temperature is provided from 150°C to 200°C during the forming step of the molding compound to transform the B-stage film layer into a C-stage film layer.

Claim 15. (Original) The process in accordance with claim 11, wherein the glass transition temperature (T_g) of the B-stage film layer is higher than -10°C.

Application No. 10/721,288

Claim 16. (Original) The process in accordance with claim 11, wherein the chip-attaching surface of the substrate is smaller than 1.5 times the active surface of the chip in area.

Claims 17-18. (Canceled)